



## 1N50-MS

Preliminary

Power MOSFET

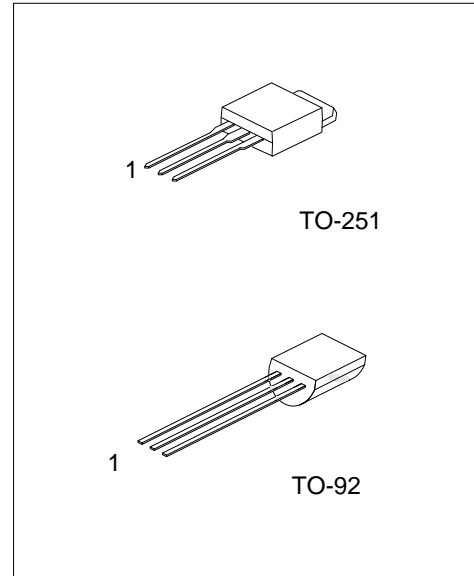
### 1A, 500V N-CHANNEL POWER MOSFET

#### DESCRIPTION

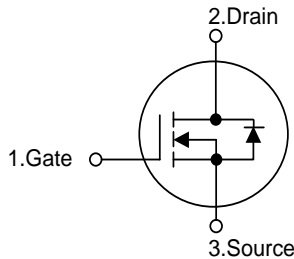
The UTC 1N50-MS is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

#### FEATURES

- \*  $R_{DS(ON)} \leq 8.5 \Omega @ V_{GS}=10V, I_D=0.5A$
- \* Fast switching capability
- \* Avalanche energy tested
- \* Improved dv/dt capability, high ruggedness



#### SYMBOL



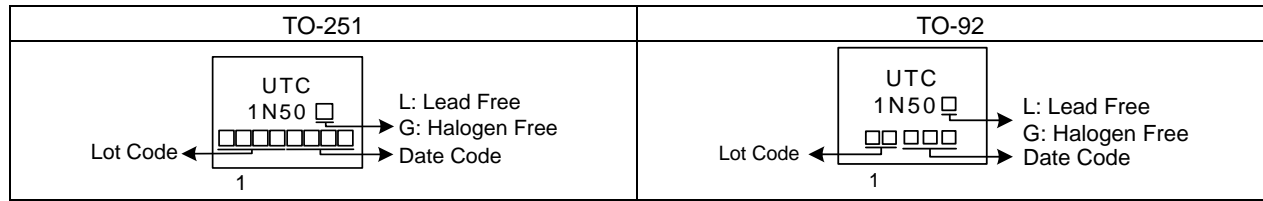
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1N50L-TM3-T	1N50G-TM3-T	TO-251	G	D	S	Tube
1N50L-T92-B	1N50G-T92-B	TO-92	B	C	E	Tape Box
1N50L-T92-K	1N50G-T92-K	TO-92	B	C	E	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N50G-TM3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube, B: Tape Box, K: Bulk</p> <p>(2) TM3: TO-251, T92: TO-92</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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### MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	500	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Continuous Drain Current		$I_D$	1	A
Pulsed Drain Current (Note 2)		$I_{DM}$	2	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	38	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-251	$P_D$	25	W
	TO-92		2.7	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 30\text{mH}$ ,  $I_{AS} = 1.6\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 1.0\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-251	$\theta_{JA}$	110	$^\circ\text{C}/\text{W}$
	TO-92		160 (Note)	$^\circ\text{C}/\text{W}$
Junction to Case	TO-251	$\theta_{JC}$	5 (Note)	$^\circ\text{C}/\text{W}$
	TO-92		45 (Note)	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

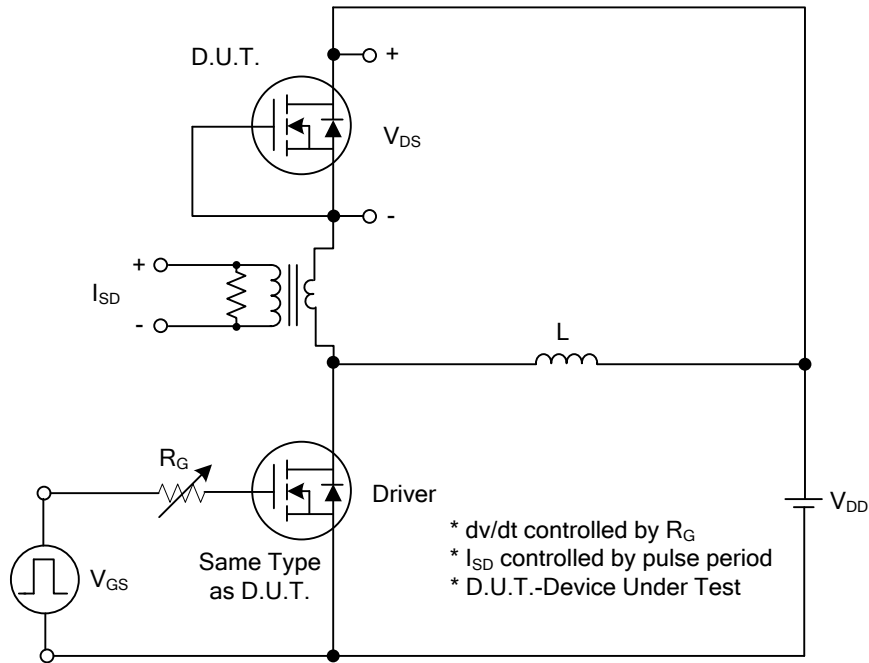
■ **ELECTRICAL CHARACTERISTICS** ( $T_J=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	500			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=500V, V_{GS}=0V$			10	$\mu A$
Gate- Source Leakage Current	Forward	$V_{GS}=30V, V_{DS}=0V$			100	nA
	Reverse		$V_{GS}=-30V, V_{DS}=0V$			-100
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.5A$			8.5	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{MHz}$		86		pF
Output Capacitance	$C_{OSS}$			18		pF
Reverse Transfer Capacitance	$C_{RSS}$			2		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	$Q_G$	$V_{DS}=400V, V_{GS}=10V, I_D=1A$ $I_G=1\text{mA}$ (Note 1, 2)		3.6		nC
Gate-Source Charge	$Q_{GS}$			1.8		nC
Gate-Drain Charge	$Q_{GD}$			0.4		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=100V, V_{GS}=10V, I_D=1A,$ $R_G=25\Omega$ (Note 1, 2)		3		ns
Turn-On Rise Time	$t_R$			16		ns
Turn-Off Delay Time	$t_{D(OFF)}$			11		ns
Turn-Off Fall Time	$t_F$			29		ns
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Maximum Body-Diode Continuous Current	$I_S$				1	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				2	A
Drain-Source Diode Forward Voltage (Note 1)	$V_{SD}$	$I_S=1A, V_{GS}=0V$			1.4	V
Reverse Recovery Time (Note 1)	$t_{rr}$	$I_S=1A, V_{GS}=0V$ $di/dt=100A/\mu s$		145		ns
Reverse Recovery Charge	$Q_{rr}$			0.86		$\mu C$

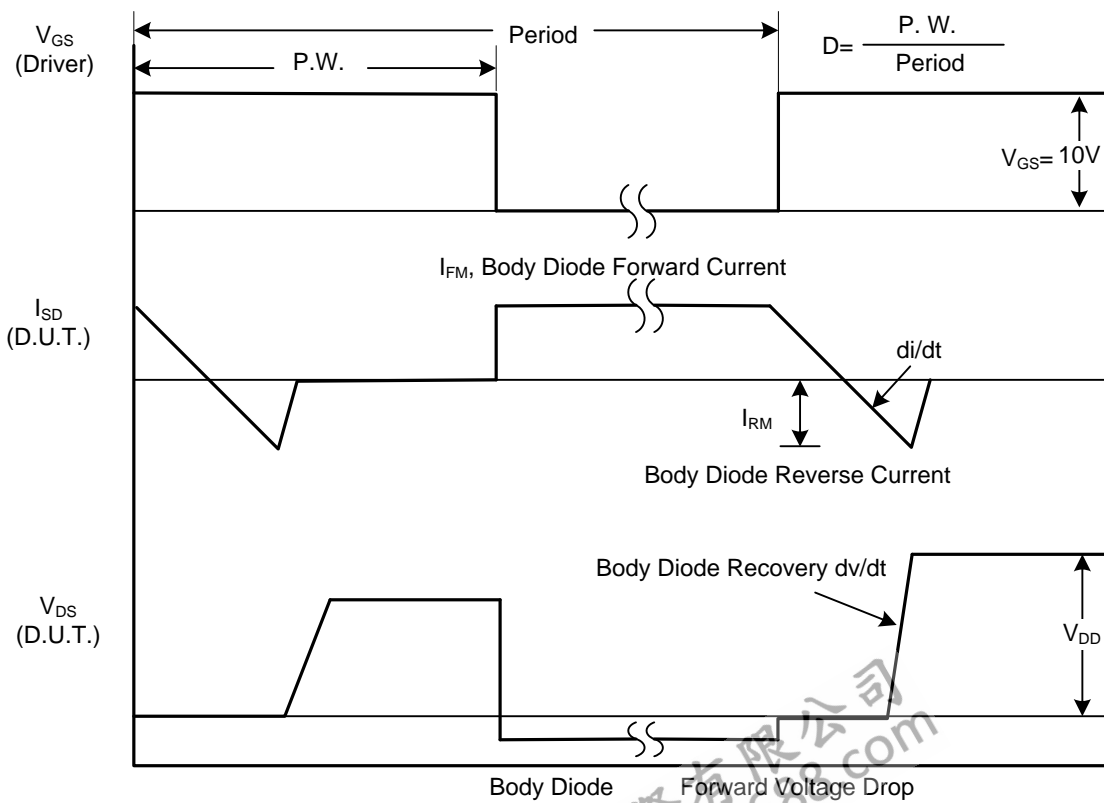
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

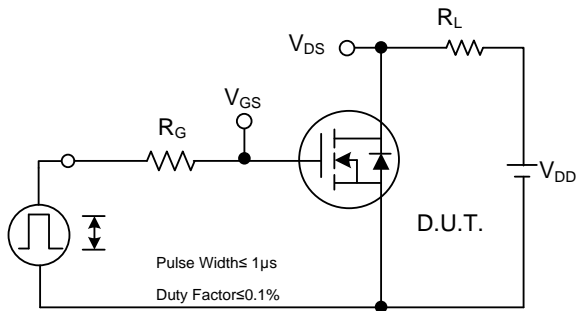


Peak Diode Recovery dv/dt Test Circuit

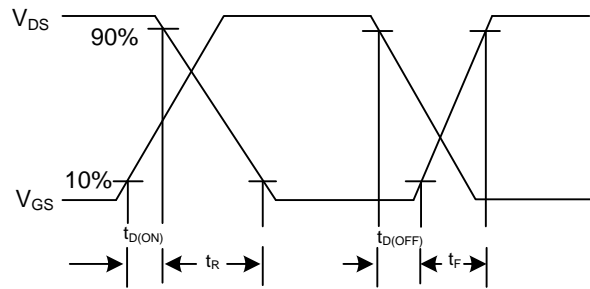


Peak Diode Recovery dv/dt Waveforms

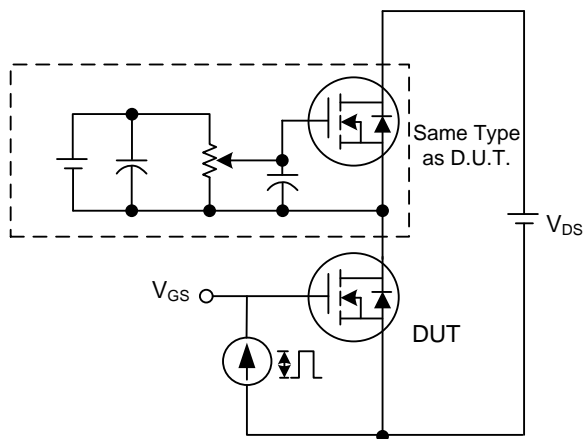
■ TEST CIRCUITS AND WAVEFORMS



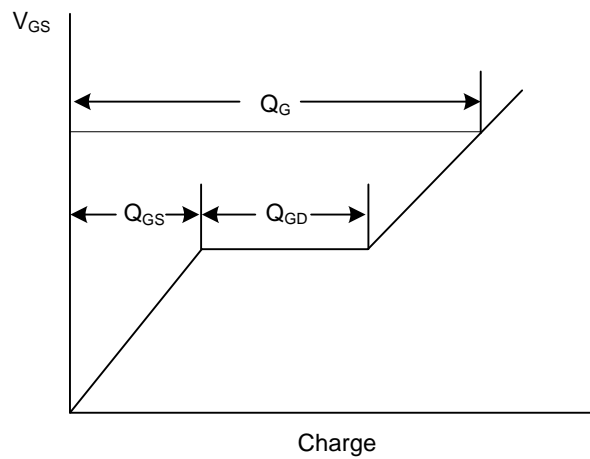
Switching Test Circuit



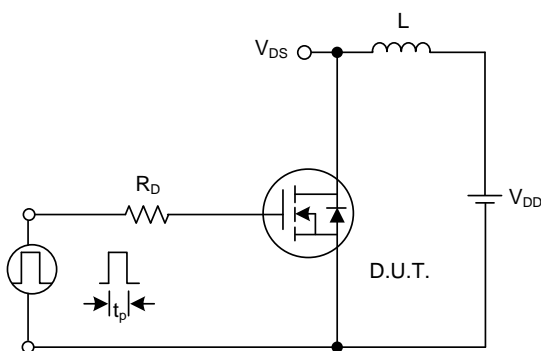
Switching Waveforms



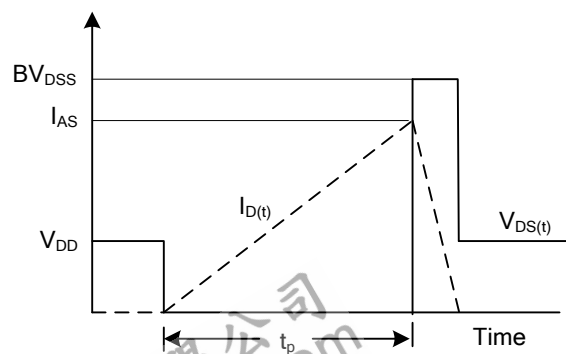
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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